



## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

- $V_{DS}$  40V
- $I_D$  110A
- $R_{DS(ON)}$  ( at  $V_{GS}=10V$ ) 1.9m $\Omega$
- 100% EAS Tested
- 100%  $V_{DS}$  Tested

### General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

-



■



## Typical Electrical and Thermal Characteristics Diagrams

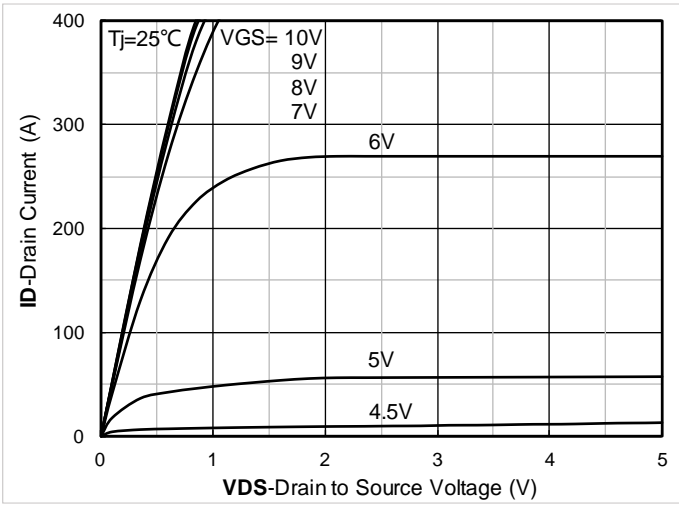


Figure 1. Output Characteristics

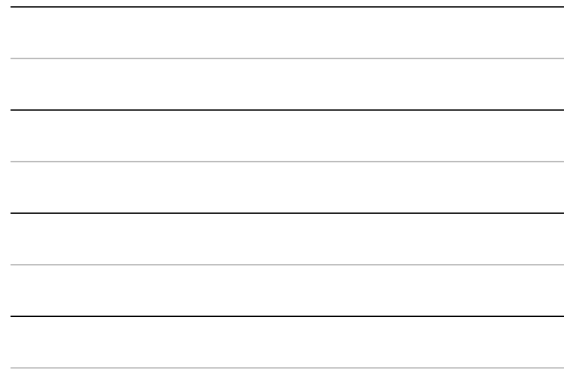


Figure 2. Transfer Characteristics

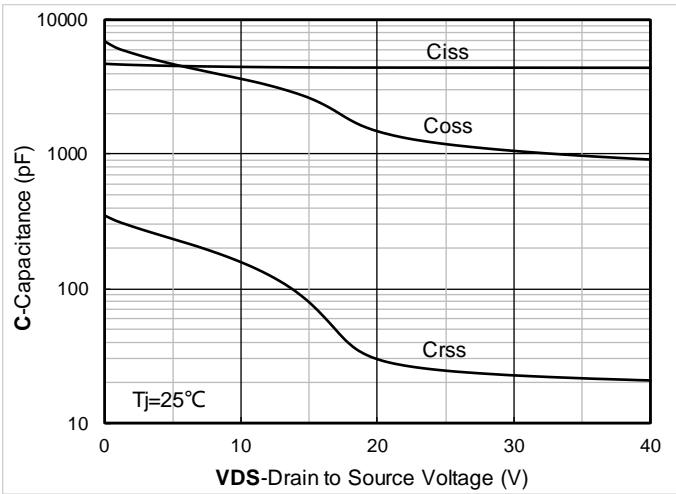


Figure 3. Capacitance Characteristics

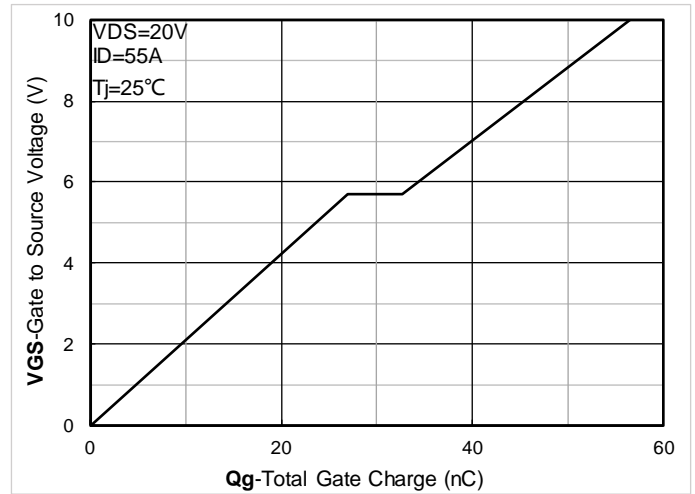


Figure 4. Gate Charge

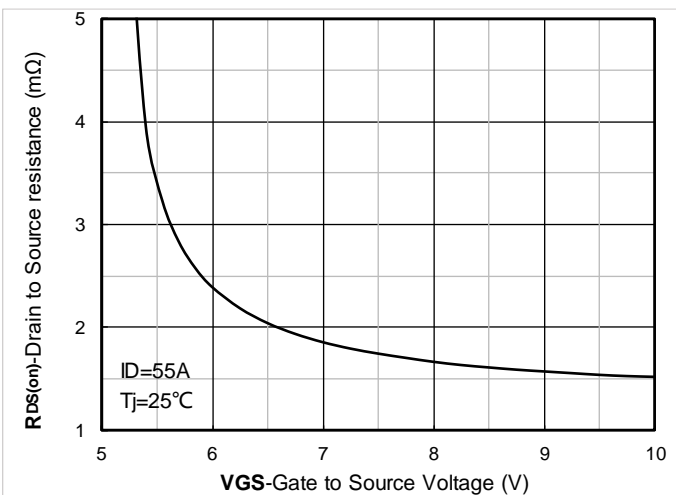


Figure 5. On-Resistance vs Gate to Source Voltage

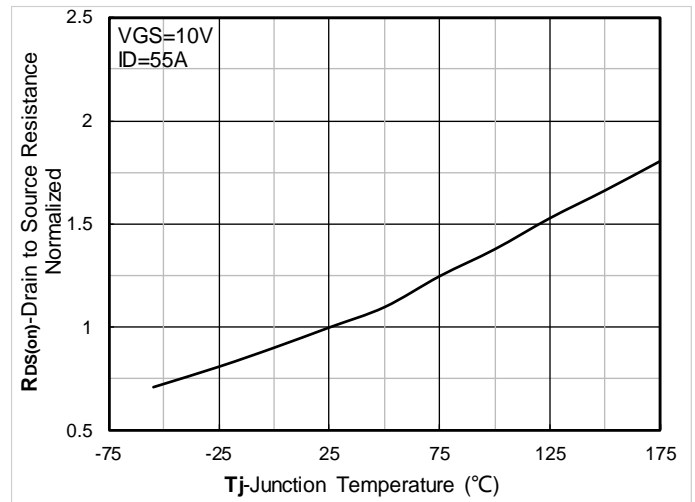


Figure 6. Normalized On-Resistance



# YJG110G04H

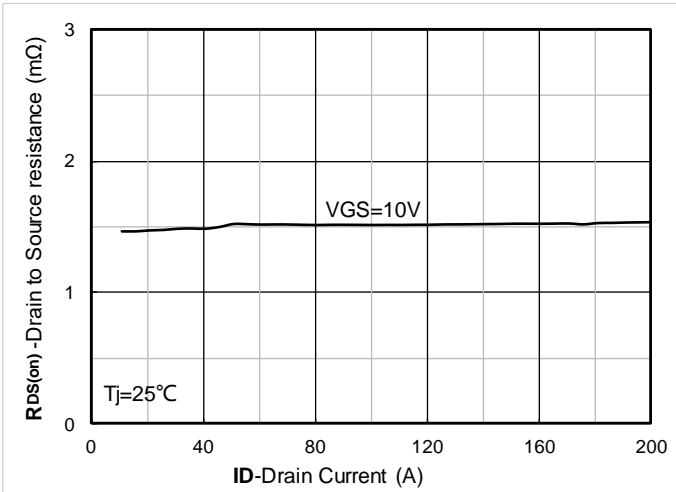


Figure 7.  $R_{DS(on)}$  VS Drain Current

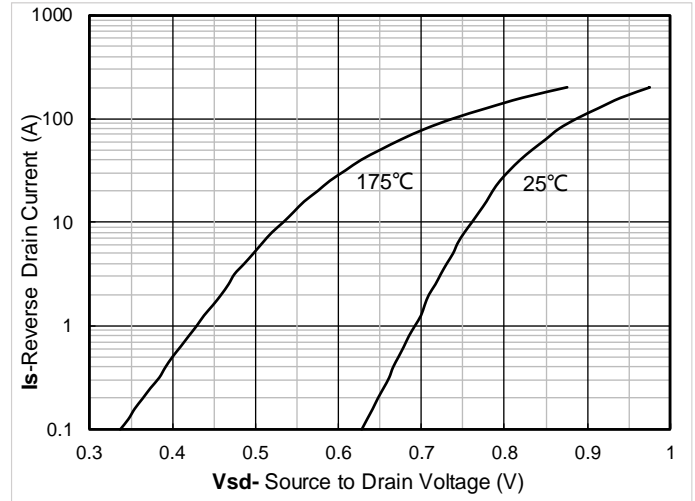


Figure 8. Forward characteristics of reverse diode

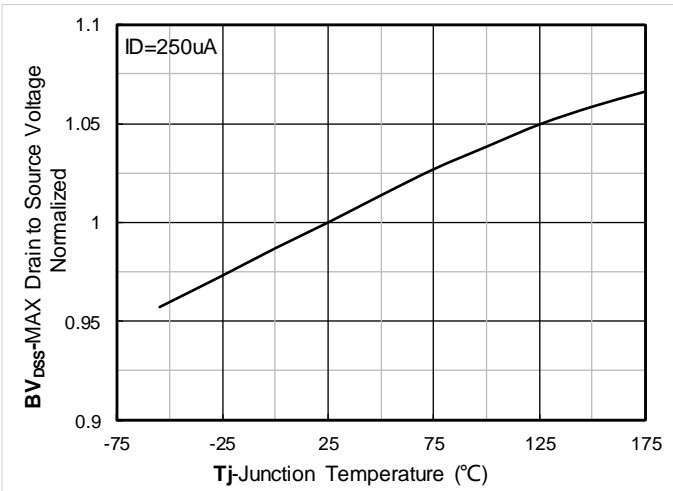


Figure 9. Normalized breakdown voltage

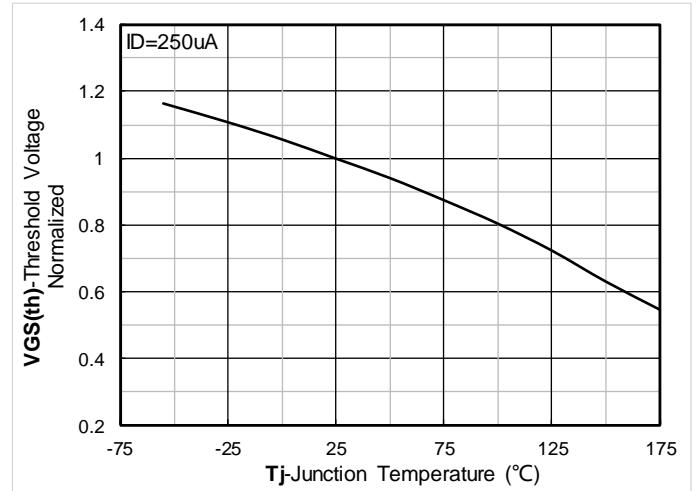


Figure 10. Normalized Threshold voltage

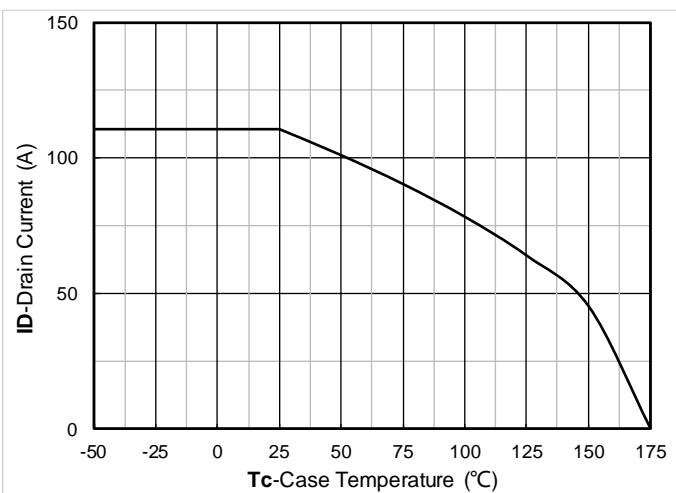


Figure 11. Current dissipation

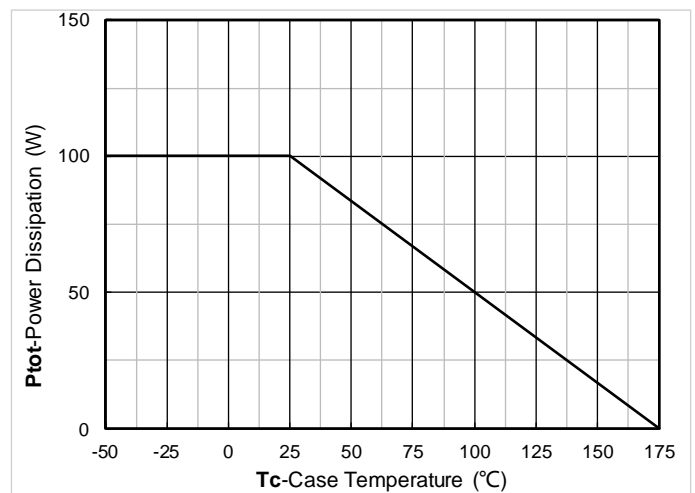


Figure 12. Power dissipation

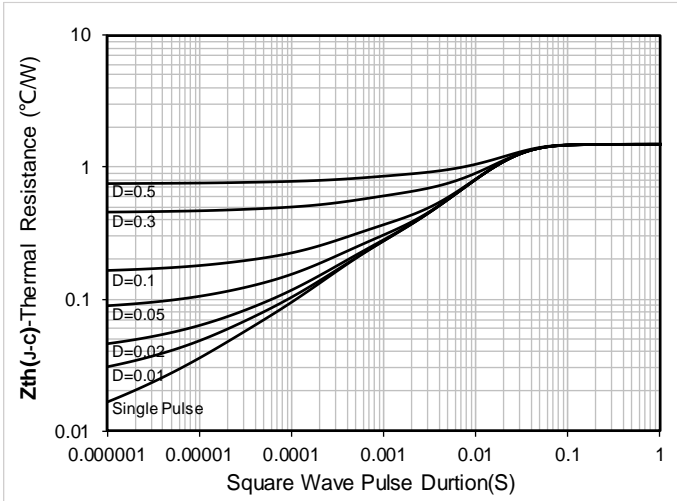


Figure 13. Maximum Transient Thermal Impedance

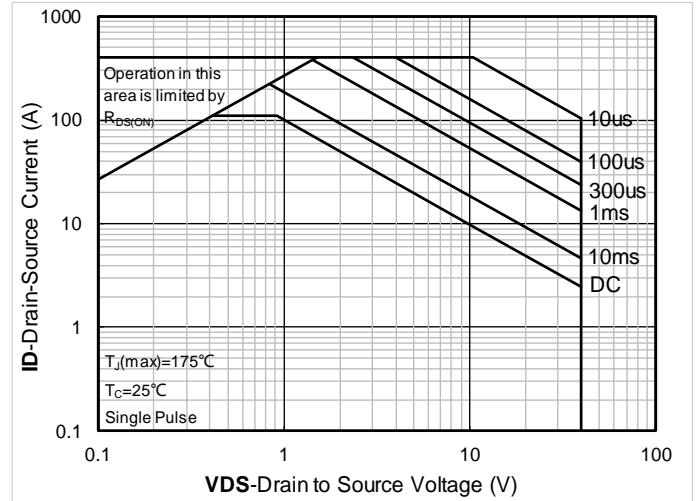


Figure 14. Safe Operation Area

## ■ Test Circuits & Waveforms

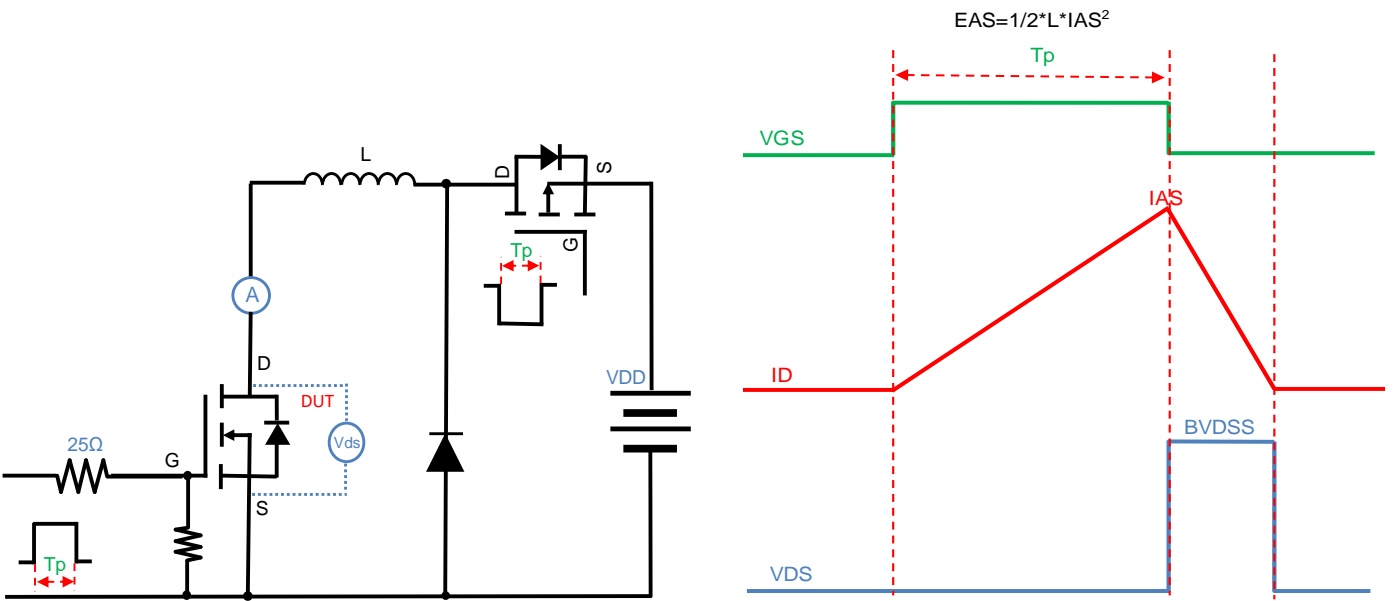


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

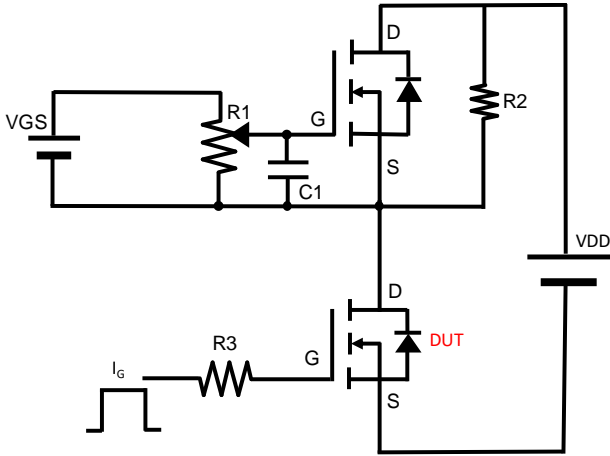


Figure B. Gate Charge Test Circuit & Waveform

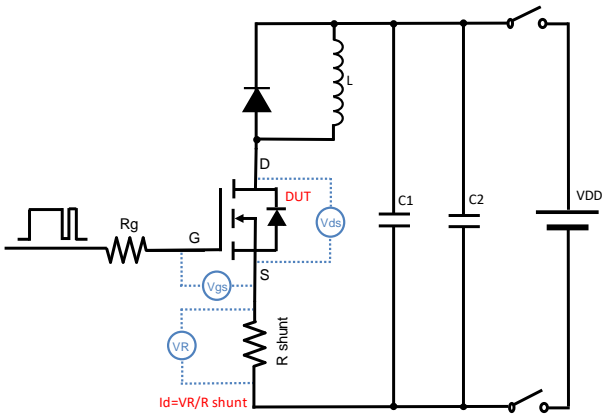


Figure C. Resistive Switching Test Circuit & Waveform

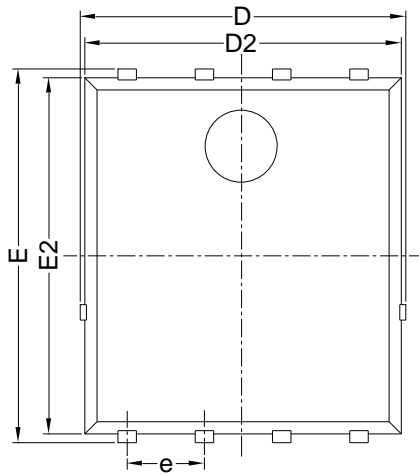


Figure D. Diode Recovery Test Circuit & Waveform

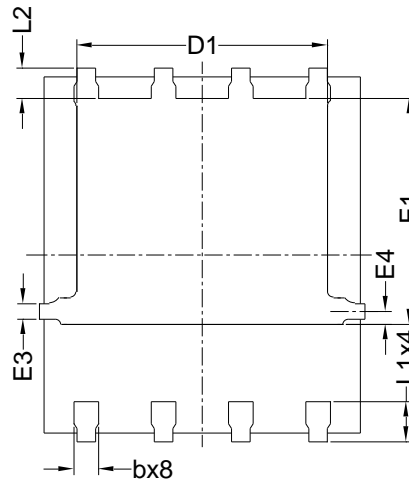


# YJG110G04H

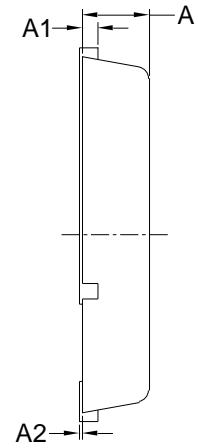
## ■ PDFN5060-8L-B-1.1MM Package information



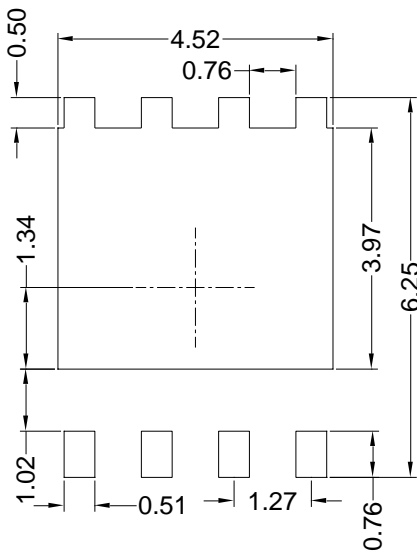
Top View



Bottom View



Side View



Suggested Solder Pad Layout  
Top View

| SYMBOL | MILLIMETER |      |      |
|--------|------------|------|------|
|        | MIN        | NOM  | MAX  |
| D      | 5.15       | 5.35 | 5.55 |
| E      | 5.95       | 6.15 | 6.35 |
| A      | 1.00       | 1.10 | 1.20 |
| A1     | 0.254 BSC  |      |      |
| A2     |            |      | 0.10 |
| D1     | 3.92       | 4.12 | 4.32 |
| E1     | 3.52       | 3.72 | 3.92 |
| D2     | 5.00       | 5.20 | 5.40 |
| E2     | 5.66       | 5.86 | 6.06 |
| E3     | 0.254 REF  |      |      |
| E4     | 0.21 REF   |      |      |
| L1     | 0.56       | 0.66 | 0.76 |
| L2     | 0.50 BSC   |      |      |
| b      | 0.31       | 0.41 | 0.51 |
| e      | 1.27 BSC   |      |      |

Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.10$  mm.
3. The pad layout is for reference purposes only.



# YJG110G04H

---

## Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with automotive electronics, are not designed for use in medical, life-saving, lifesustaining, or military, Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.